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List of Publications by Year in Descending Order

37 papers	760 citations	15 h-index	27 g-index
37 ext. papers	873 ext. citations	2.6 avg, IF	3.95 L-index

#	Paper	IF	Citations
37	Identification of Current Transport Mechanisms and Temperature Sensing Qualifications for Al/(ZnS-PVA)/p-Si Structures at Low and Moderate Temperatures. *IEEE Sensors Journal*, **2022**, 22, 99-106	4	4
36	Enhancement of Nonlinear Absorption in Defect Controlled ZnO Polycrystalline Thin Films by Means of Co-Doping. *Physica Status Solidi (B): Basic Research*, **2021**, 258, 2000539	1.3	2
35	Comparison of characteristic properties of Al, Ga, and In-doped ZnO thin films formed by sol-gel method. *Superlattices and Microstructures*, **2021**, 159, 107034	2.8	0
34	High quality optoelectronic properties of Sb-doped SnO2 by spray pyrolysis with less solution. *Materials Research Express*, **2019**, 6, 086423	1.7	4
33	Investigation of the structural and optical properties of copper-titanium oxide thin films produced by changing the amount of copper. *Thin Solid Films*, **2019**, 685, 293-298	2.2	3
32	Comprehensive structural analysis and electrical properties of (Cu, Al and In)-doped SnO2 thin films. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2019**, 251, 114445	3.1	9
31	Monitoring the characteristic properties of Ga-doped ZnO by Raman spectroscopy and atomic scale calculations. *Journal of Molecular Structure*, **2019**, 1180, 505-511	3.4	29
30	Determination of the critical carrier concentration for the metal–insulator transition in Ga-doped ZnO. *Journal of Materials Science: Materials in Electronics*, **2018**, 29, 14111-14115	2.1	9
29	Effects of Co and Cu dopants on the structural, optical, and electrical properties of ZnO nanocrystals. *Journal of Materials Science: Materials in Electronics*, **2017**, 28, 6088-6092	2.1	10
28	An Understanding of the Band Gap Shrinkage in Sn-Doped ZnO for Dye-Sensitized Solar Cells. *Journal of Electronic Materials*, **2017**, 46, 6739-6744	1.9	10
27	Al and X (Sn, Cu, In) co-doped ZnO nanocrystals. *Journal of Materials Science: Materials in Electronics* , **2016**, 27, 6179-6182	2.1	8
26	Studies on optical properties of antimony doped SnO 2 films. *Applied Surface Science*, **2015**, 352, 16-22	6.7	33
25	Influence of oxygen flow rate in CuO. *Applied Surface Science*, **2015**, 352, 155-157	6.7	3
24	Electrical And Microstructural Properties Of (Cu, Al, In)-Doped SnO2 Films Deposited By Spray Pyrolysis. *Advanced Materials Letters*, **2014**, 5, 309-314	2.4	15
23	Hopping conduction in In-doped CuO thin films. *Applied Surface Science*, **2014**, 318, 105-107	6.7	26
22	Carrier transport in In-doped CuO thin films. *Philosophical Magazine*, **2013**, 93, 3110-3117	1.6	7
21	Barrier-controlled electron transport in Sn-doped ZnO polycrystalline thin films. *Thin Solid Films*, **2012**, 522, 90-94	2.2	10

20	Fluctuating in the hopping rate of CuO thin films with respect to substrate temperature. *Superlattices and Microstructures*, **2012**, 52, 759-764	2.8	11
19	The effects of film thickness on the optical properties of TiO2SnO2compound thin films. *Physica Scripta*, **2011**, 84, 065602	2.6	42
18	Multiphonon hopping of carriers in CuO thin films. *Physica B: Condensed Matter*, **2011**, 406, 3551-3555	2.8	19
17	The change in the electrical transport mechanism from the grain boundary conduction to the nearest-neighbor hopping conduction in SnO2. *Journal of Materials Science: Materials in Electronics*, **2011**, 22, 872-875	2.1	12
16	Extraction of important electrical parameters of CuO. *Physica B: Condensed Matter*, **2011**, 406, 575-578	2.8	22
15	Estimation of compensation ratio by identifying the presence of different hopping conduction mechanisms in SnO2 thin films. *Thin Solid Films*, **2011**, 519, 2302-2307	2.2	29
14	Electrical Properties of Polycrystalline SnO$_{2}$ Thin Films. *Applied Physics Express*, **2011**, 4, 121101	2.4	9
13	The thickness effect on the electrical conduction mechanism in titanium oxide thin films. *Journal of Alloys and Compounds*, **2010**, 493, 227-232	5.7	30
12	ElectronElectron Interactions in Sb-Doped SnO2 Thin Films. *Journal of Electronic Materials*, **2010**, 39, 1152-1158	1.9	33
11	Crossover from Nearest-Neighbor Hopping Conduction to EfrosShklovskii Variable-Range Hopping Conduction in Hydrogenated Amorphous Silicon Films. *Japanese Journal of Applied Physics*, **2009**, 48, 111203	1.4	48
10	. *IEEE Sensors Journal*, **2009**, 9, 263-270	4	31
9	The role of the interface insulator layer and interface states on the current-transport mechanism of Schottky diodes in wide temperature range. *Microelectronic Engineering*, **2006**, 83, 499-505	2.5	100
8	Annealing effects on the properties of copper oxide thin films prepared by chemical deposition. *Semiconductor Science and Technology*, **2005**, 20, 398-401	1.8	160
7	Determination of the distribution of electronic states in hydrogenated amorphous germanium by capacitance techniques. *Semiconductor Science and Technology*, **2004**, 19, 270-276	1.8	2
6	Current-limiting property of Cu/cupric oxide/Cu sandwich structure. *Semiconductor Science and Technology*, **2002**, 17, 60-64	1.8	16
5	The effect of humidity on electronic conductivity of an Au/CuO/Cu2O/Cu sandwich structure. *Semiconductor Science and Technology*, **2000**, 15, 112-116	1.8	10
4	Determination of thermal annealing effect in intrinsic a-Si:H film. *Journal of Non-Crystalline Solids*, **2000**, 276, 163-168	3.9	1
3	Effect of reverse-bias annealing on thermal equilibrium changes in hydrogenated amorphous germanium. *Semiconductor Science and Technology*, **1999**, 14, 1048-1051	1.8	2

2	The thermal equilibrium changes on reverse bias annealing in Schottky diodes. *Semiconductor Science and Technology*, **1997**, 12, 1451-1454	1.8	1
1	The investigation of an annealing effect on the density of states in a-Si:H film. *Semiconductor Science and Technology*, **1997**, 12, 291-295	1.8	